



Konstantin Novoselov

## LETTERS

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nature  
nanotechnology

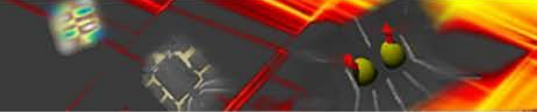
# Twist-controlled resonant tunnelling in graphene/boron nitride/graphene heterostructures

2014

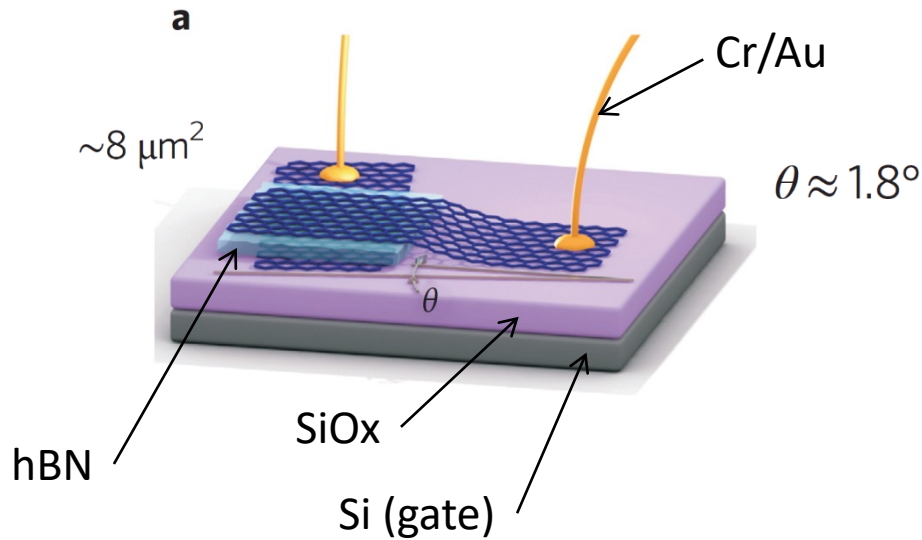
A. Mishchenko<sup>1</sup>, J. S. Tu<sup>2</sup>, Y. Cao<sup>2</sup>, R. V. Gorbachev<sup>2</sup>, J. R. Wallbank<sup>3</sup>, M. T. Greenaway<sup>4</sup>, V. E. Morozov<sup>1</sup>, S. V. Morozov<sup>5</sup>, M. J. Zhu<sup>1</sup>, S. L. Wong<sup>1</sup>, F. Withers<sup>1</sup>, C. R. Woods<sup>1</sup>, Y.-J. Kim<sup>2,6</sup>, K. Watanabe<sup>7</sup>, T. Taniguchi<sup>7</sup>, E. E. Vdovin<sup>4,5</sup>, O. Makarovskiy<sup>4</sup>, T. M. Fromhold<sup>4</sup>, V. I. Fal'ko<sup>3</sup>, A. K. Geim<sup>1,2</sup>, L. Eaves<sup>1,4</sup> and K. S. Novoselov<sup>1\*</sup>

Taras Patlatiuk

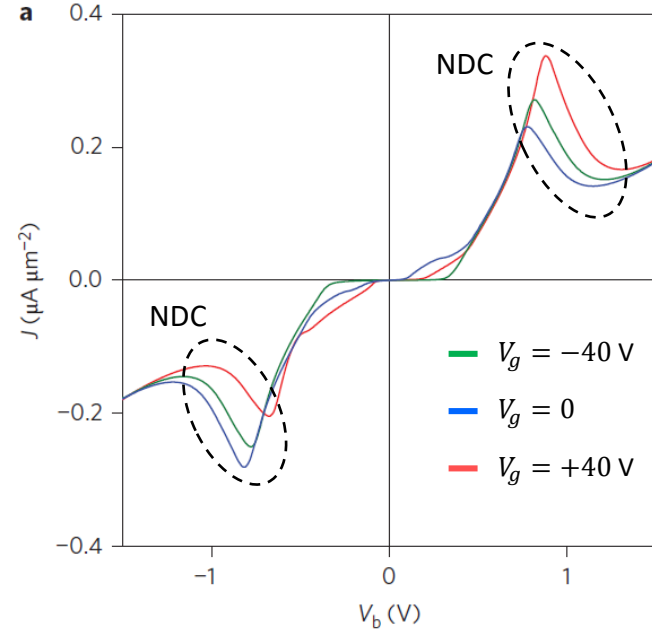
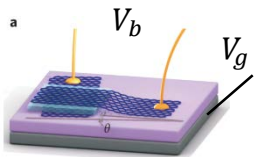
23.11.2018



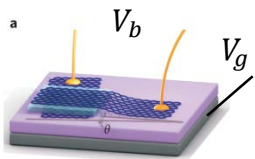
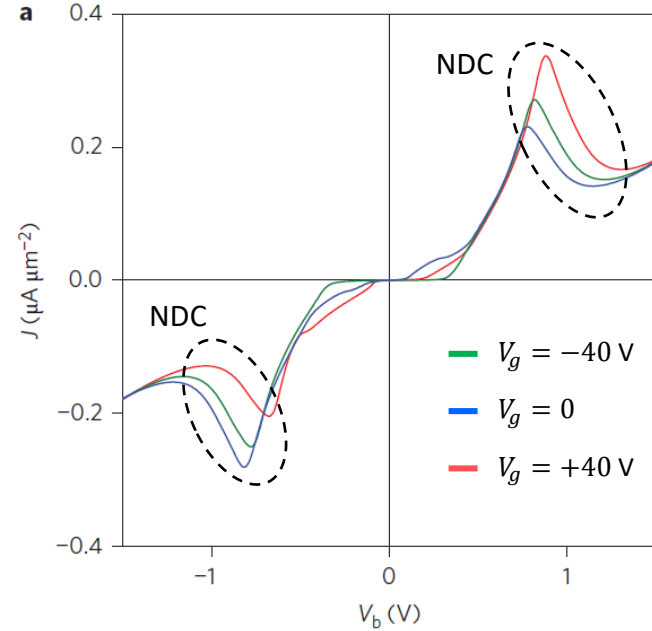
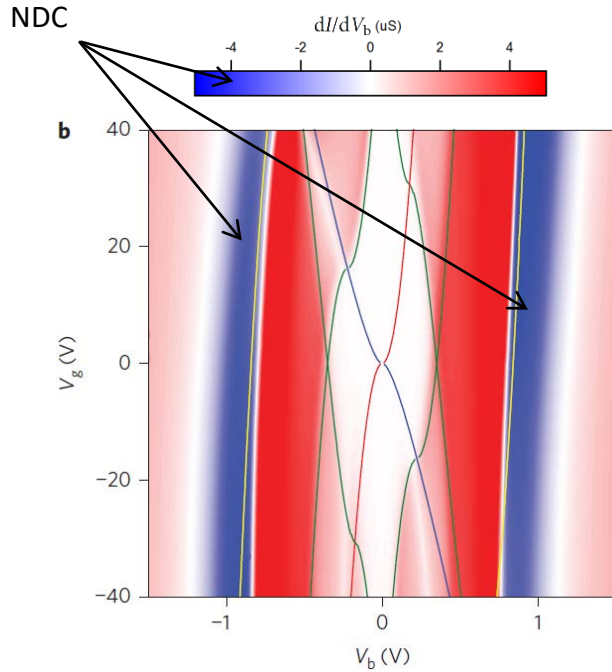
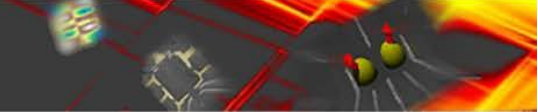
- Graphene-based high-frequency electronics
- Tunneling with conservation of energy and momentum
- Negative differential conductance (NDC)



hBN thickness 1.4 nm (four layers)

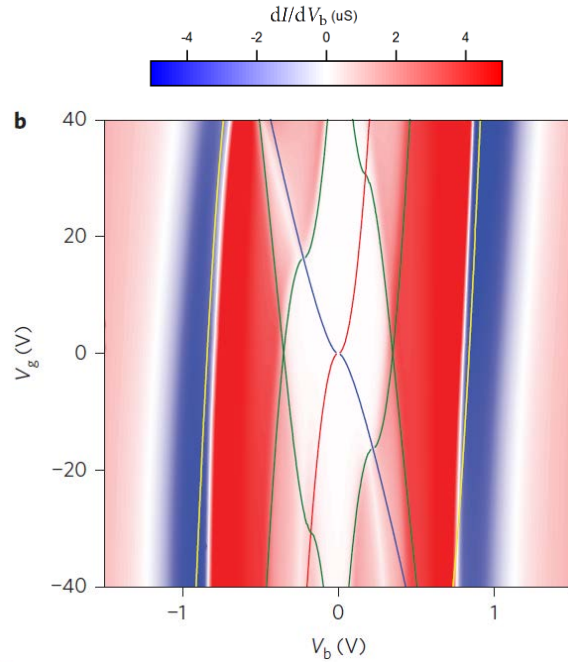


# Differential conductance

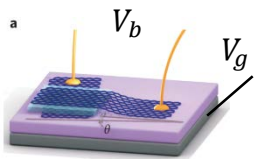
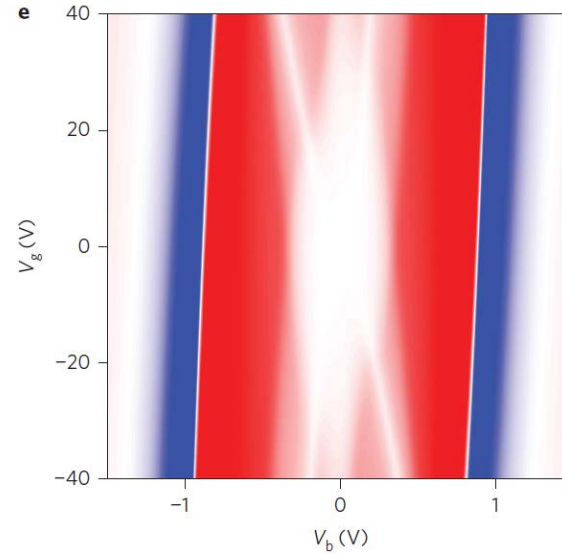




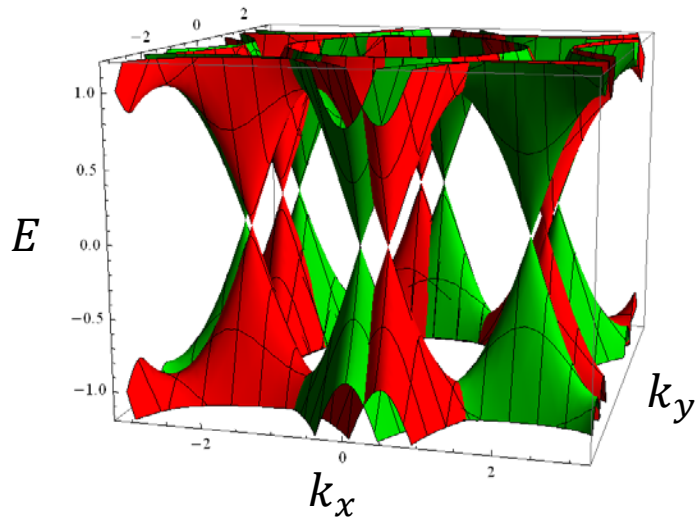
## Experiment



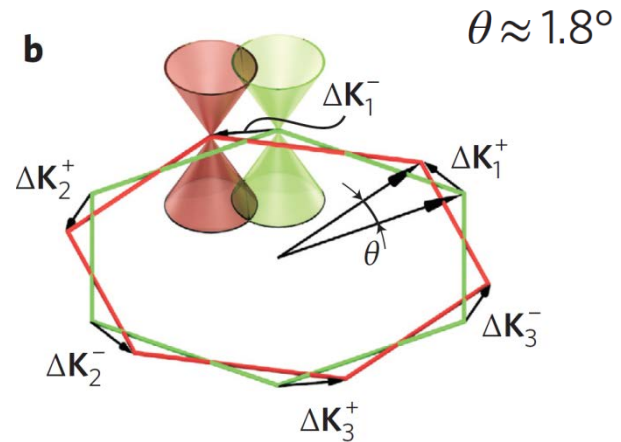
## Simulations



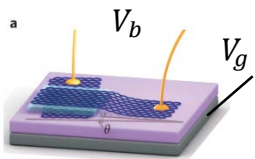
# Band structure

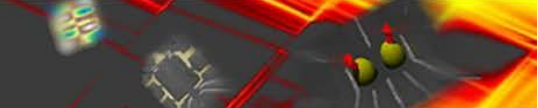


$$\theta = \hbar / \beta_0$$

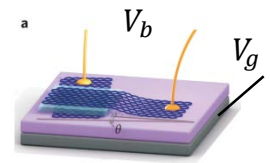
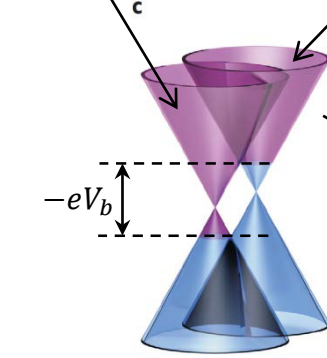


$$\Delta \mathbf{K}_i^\pm = \mathbf{l}_z \times \theta \mathbf{K}_i^\pm$$

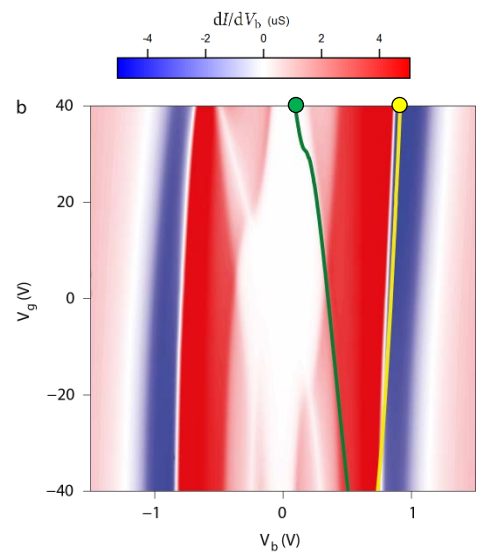
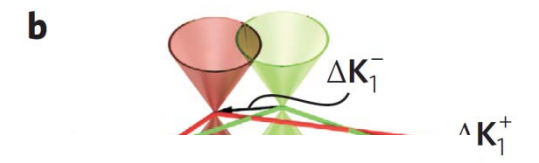
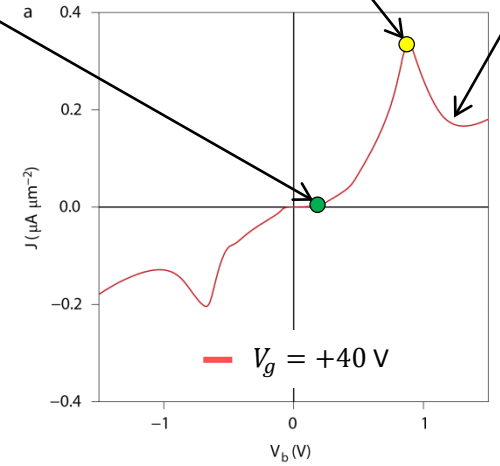
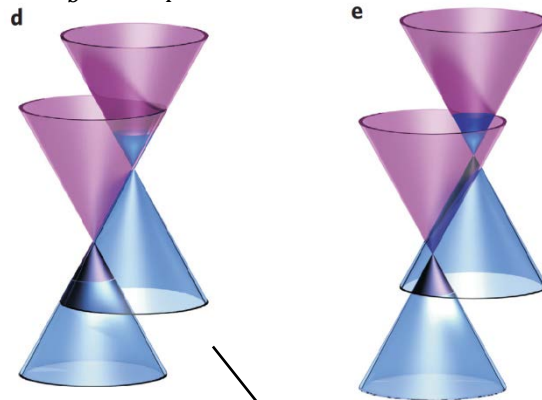




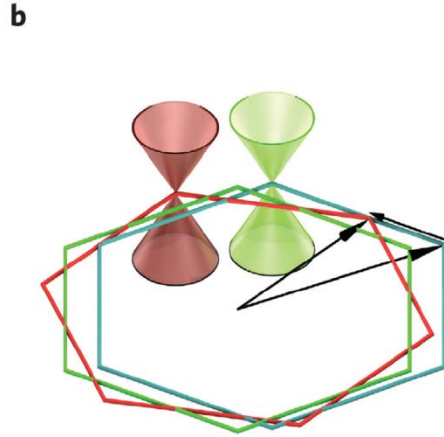
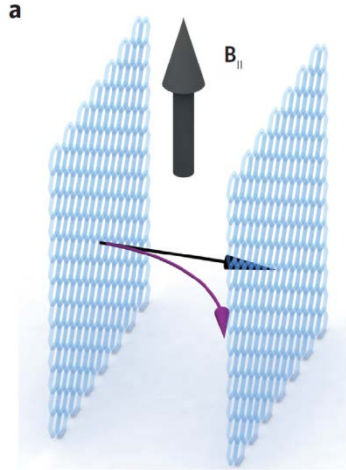
top graphene  
bottom graphene



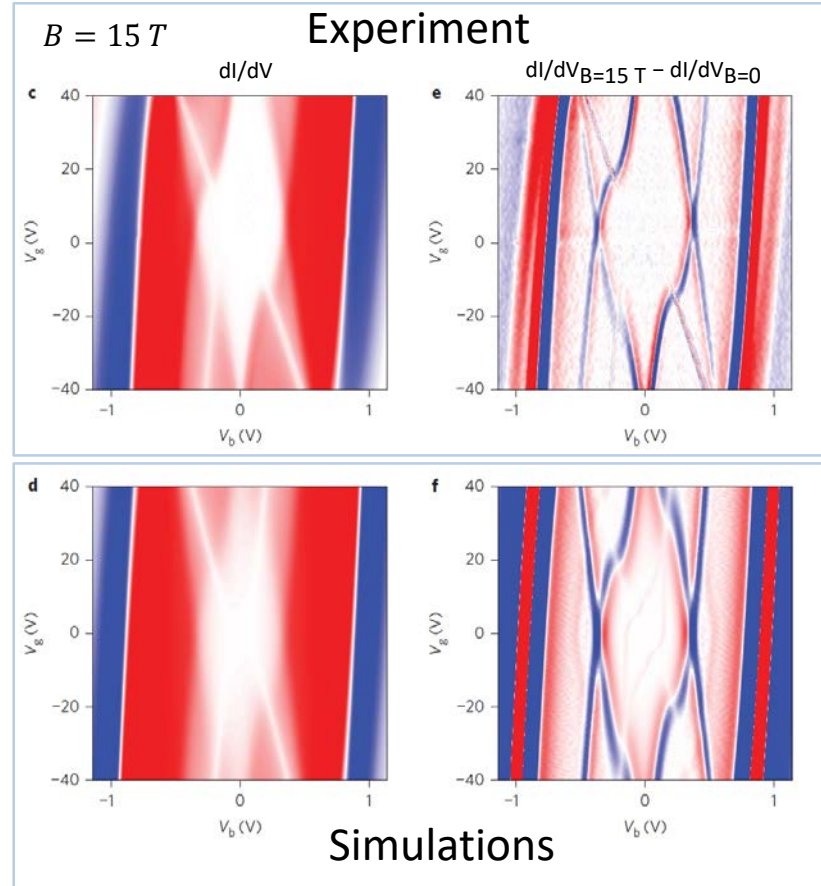
$$-eV_b = \hbar v_F \Delta K$$



# Magnetic field

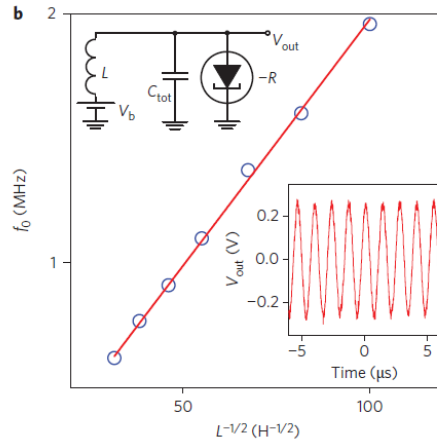
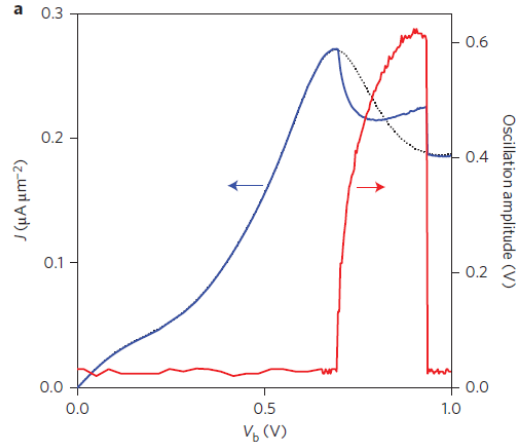


$$\hbar\Delta\mathbf{K}_i^\pm = \mathbf{I}_z \times [\theta\hbar\mathbf{K}_i^\pm + ed\mathbf{B}_\parallel]$$





# NDC oscillator



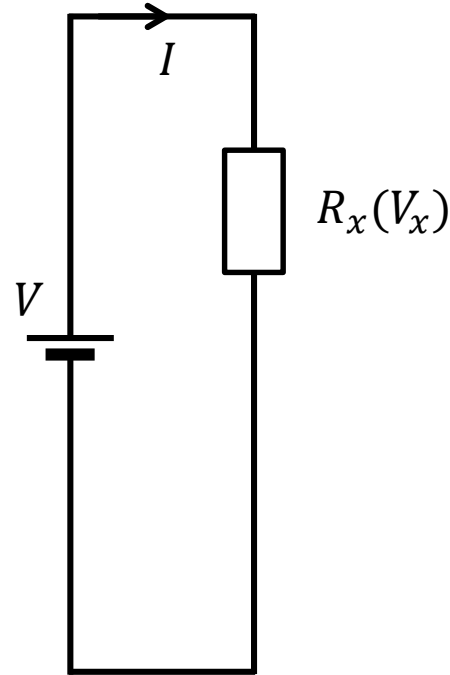
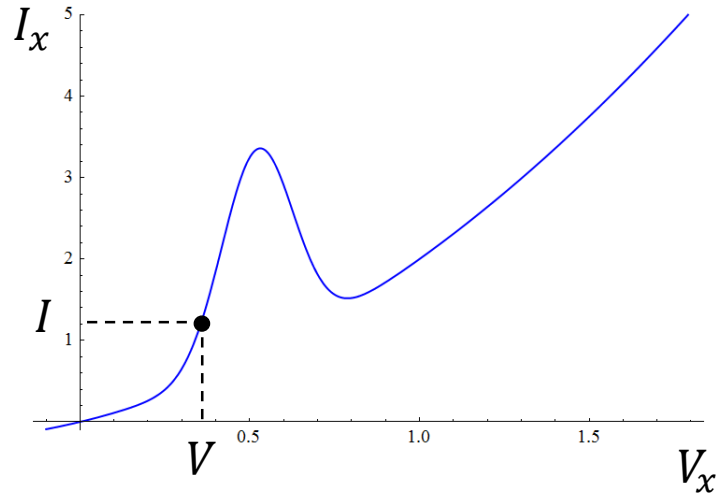
$$f_0 = \frac{1}{2\pi\sqrt{L C_{tot}}} \quad C_{tot} = 65 \text{ pF}$$

- $f_0 \sim \text{MHz}$
- parasitic capacitance limits  $f_0$   
(contact pads to Si gate)
- no carrier dwell time limitation
- potentially can operate in  $\text{THz}$  range

$V_{\text{amp}} = 0.5 \text{ V}$

# I-V characteristic

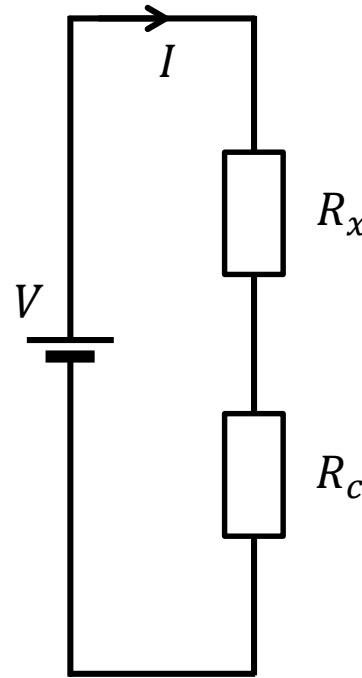
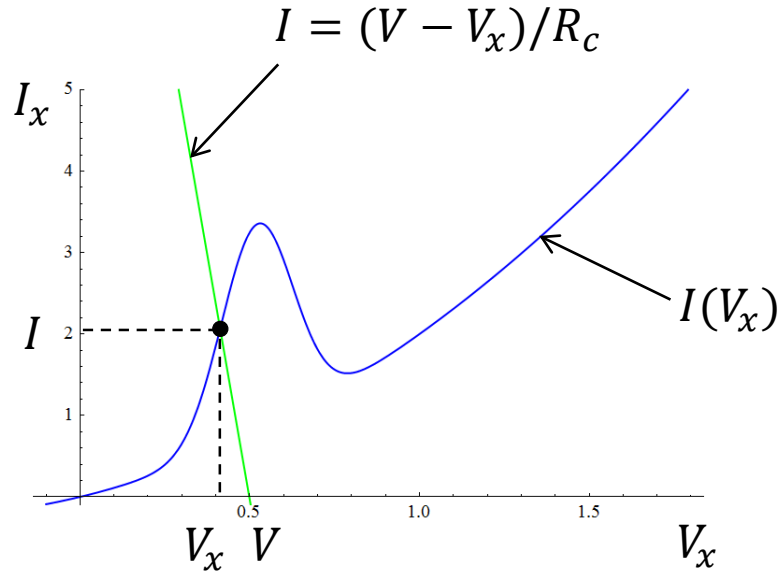
I-V characteristic of the element Rx



$$I = I_x$$

$$V = V_x$$

# Load line

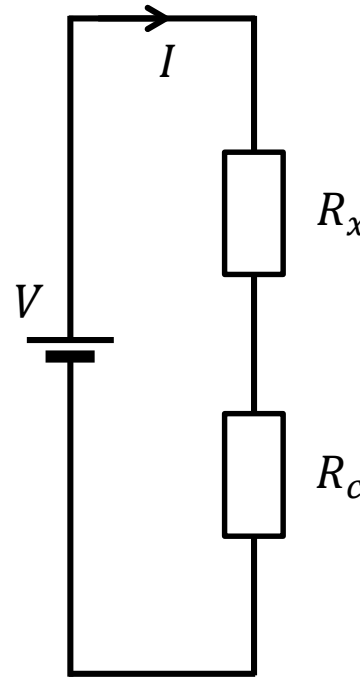
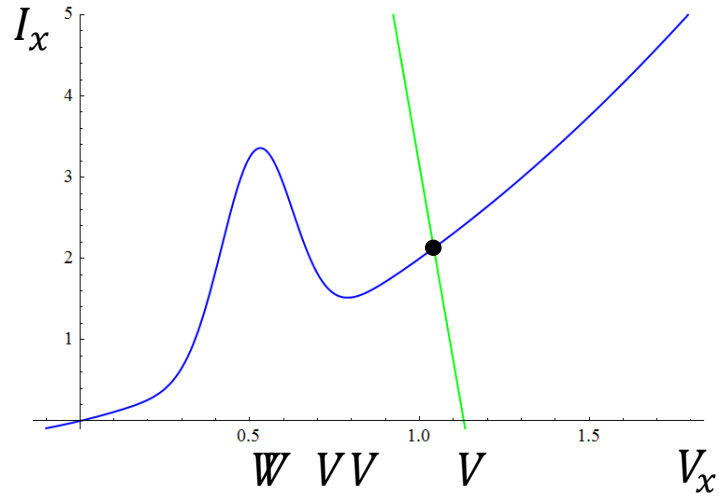


$$I = I_x$$

~~$$V = V_x$$~~

$$V = V_x + I R_c$$

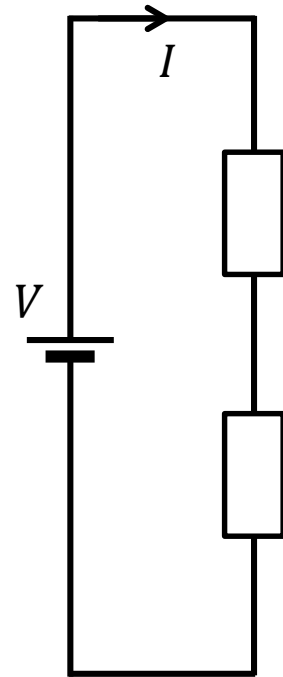
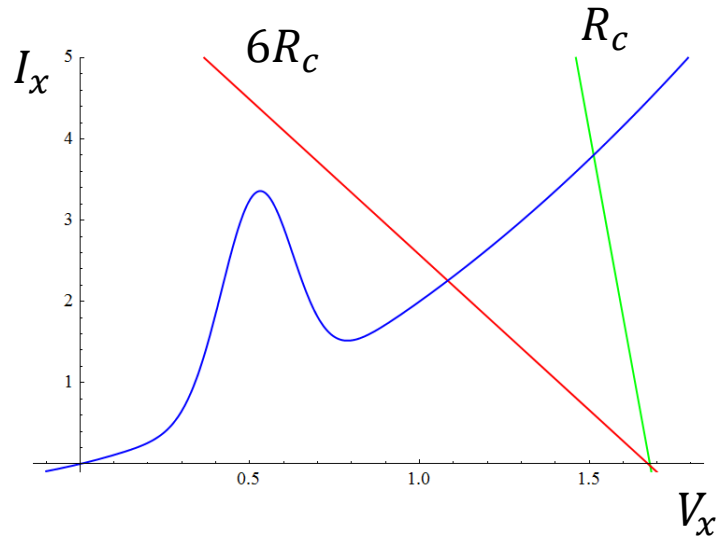
$$I = (V - V_x)/R_c$$



$$I = I_x$$

$$V = V_x + I R_c$$

$$I = (V - V_x)/R_c$$

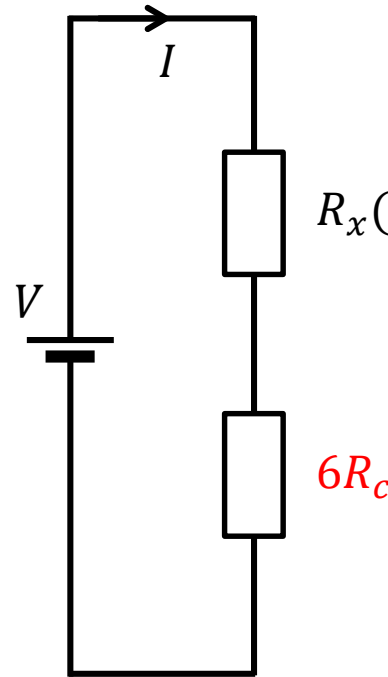
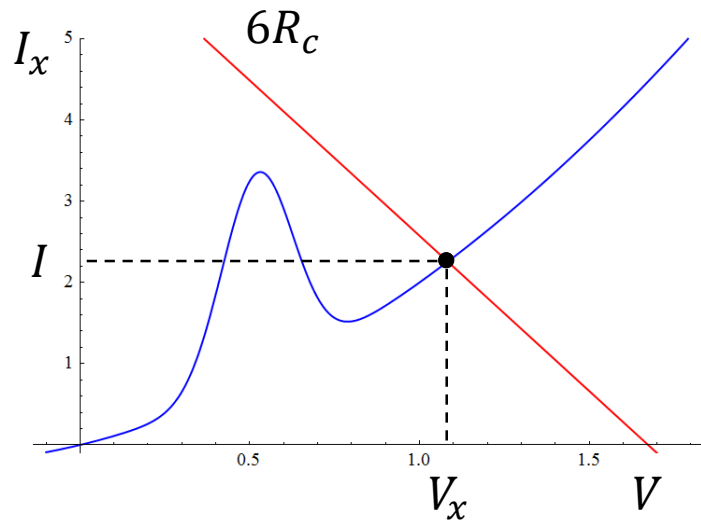


$$I = I_x$$

$$R_x(V_x) \quad V = V_x + I R_c$$

$$I = (V - V_x)/R_c$$

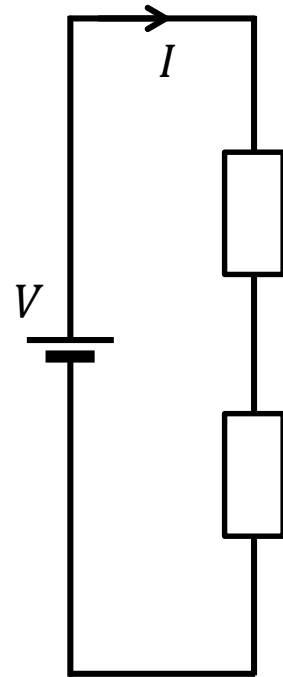
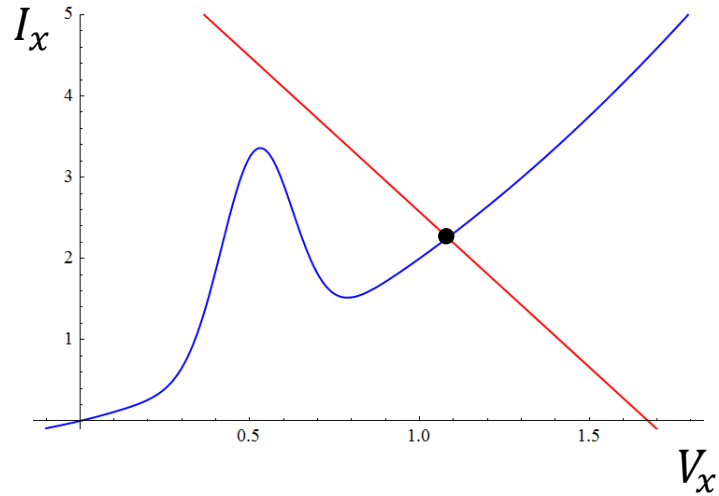
$$R_c \quad (6R_c)$$



$$I = I_x$$

$$V = V_x + I R_c$$

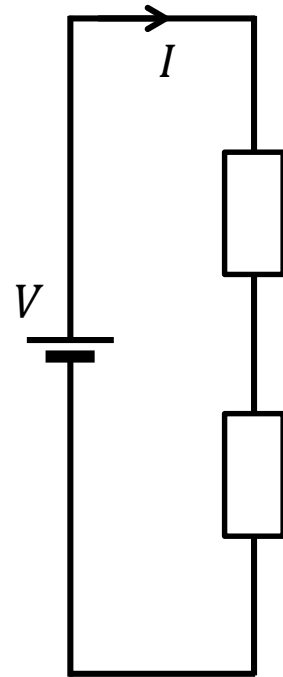
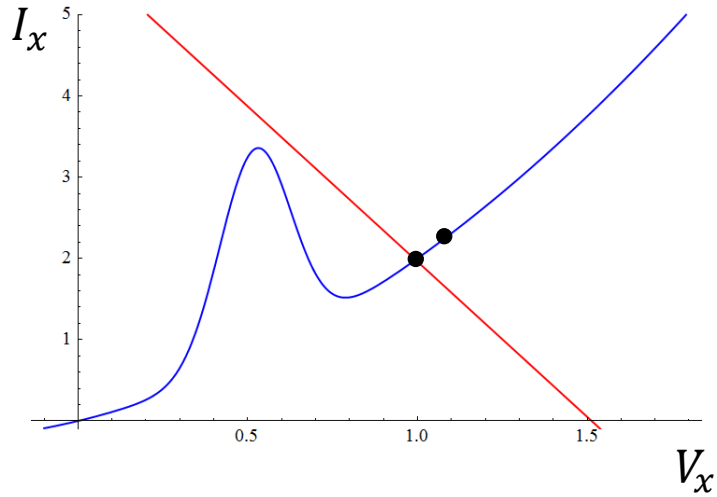
$$I = (V - V_x)/R_c$$



$$I = I_x$$

$$V = V_x + I R_c$$

$$I = (V - V_x)/R_c$$

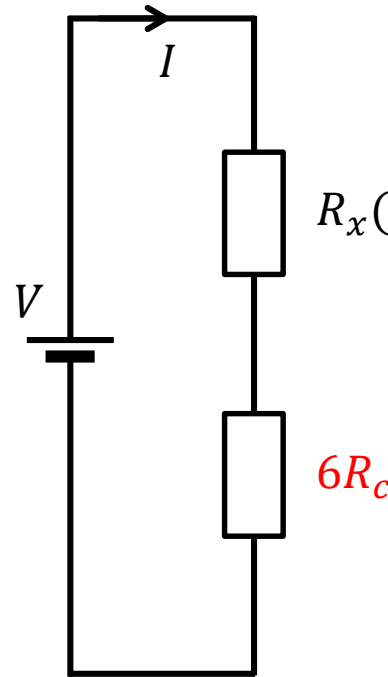
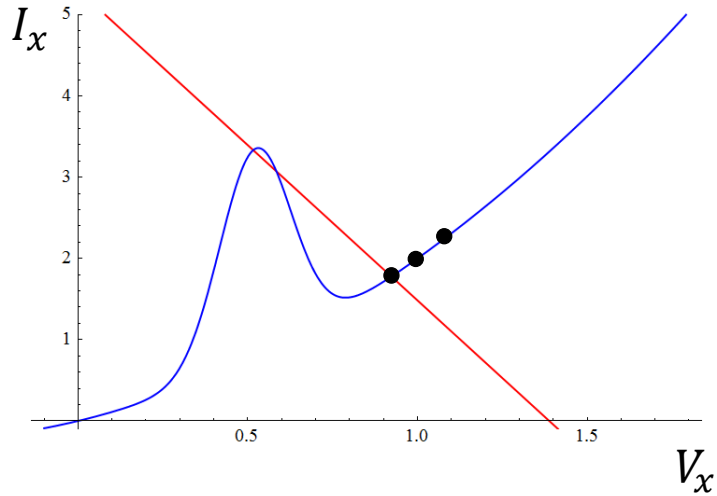


$$I = I_x$$

$$V = V_x + I R_c$$

$$I = (V - V_x)/R_c$$

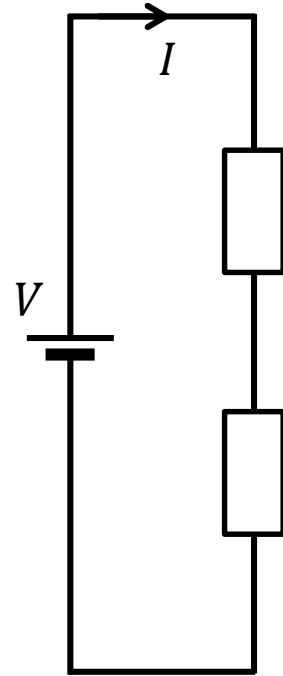
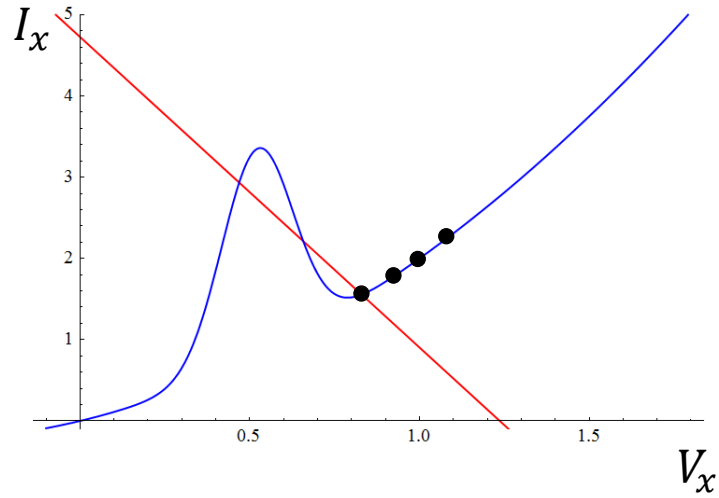




$$I = I_x$$

$$V = V_x + I R_c$$

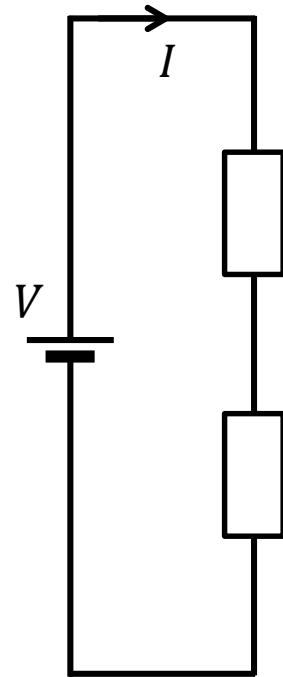
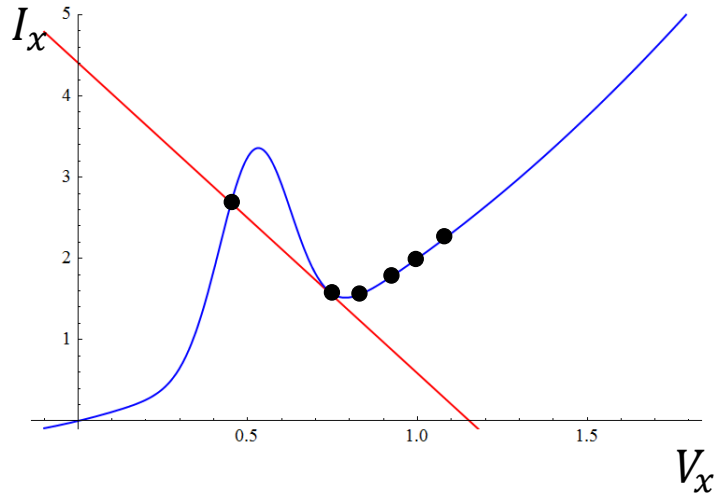
$$I = (V - V_x)/R_c$$



$$I = I_x$$

$$V = V_x + I R_c$$

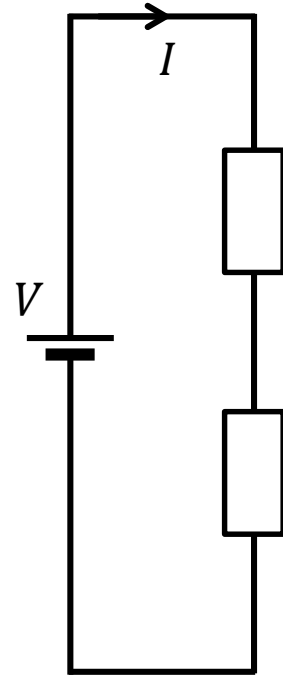
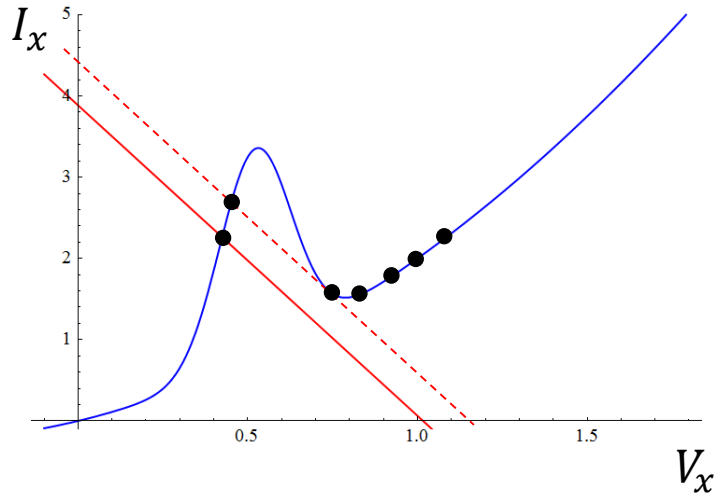
$$I = (V - V_x) / R_c$$



$$I = I_x$$

$$V = V_x + I R_c$$

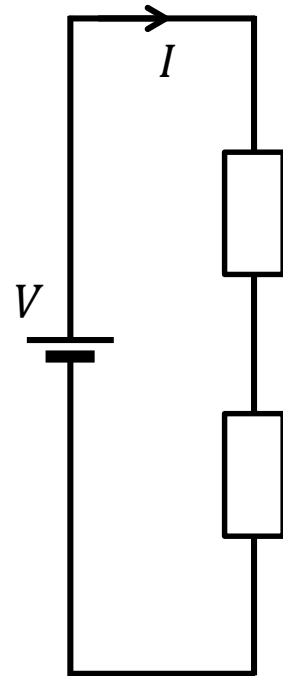
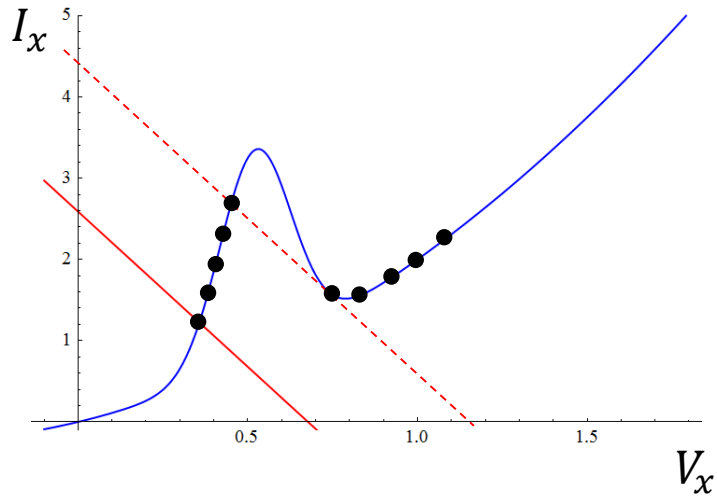
$$I = (V - V_x)/R_c$$



$$I = I_x$$

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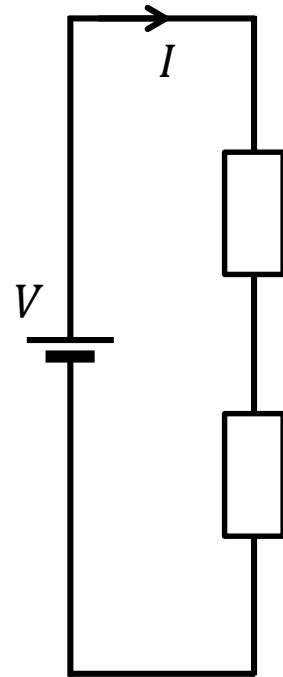
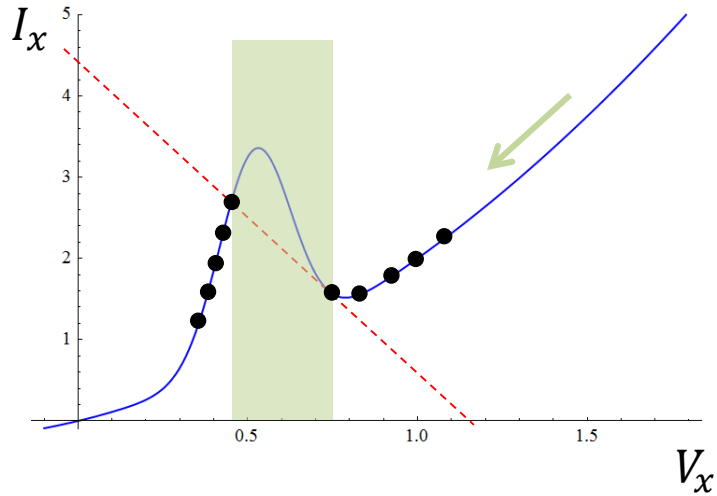
$$I = (V - V_x)/R_c$$



$$I = I_x$$

$$V = V_x + I R_c$$

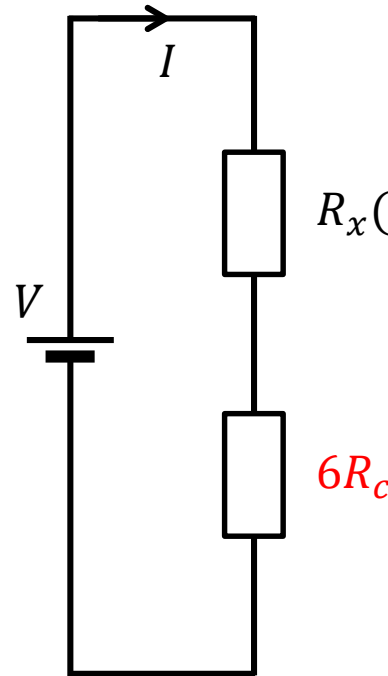
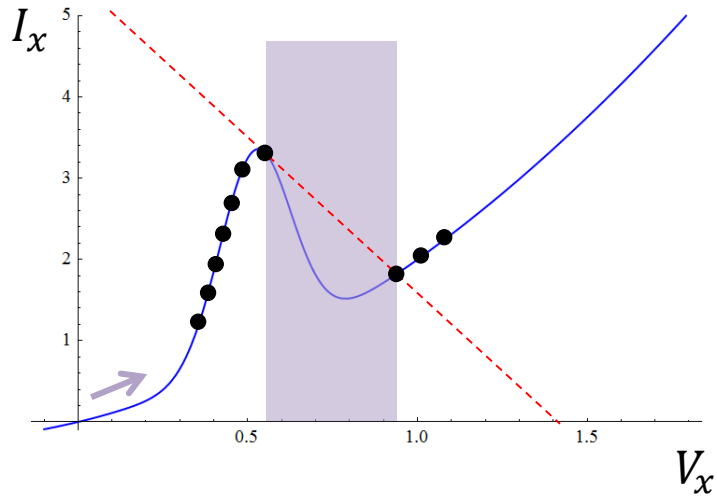
$$I = (V - V_x)/R_c$$



$$I = I_x$$

$$V = V_x + I R_c$$

$$I = (V - V_x)/R_c$$

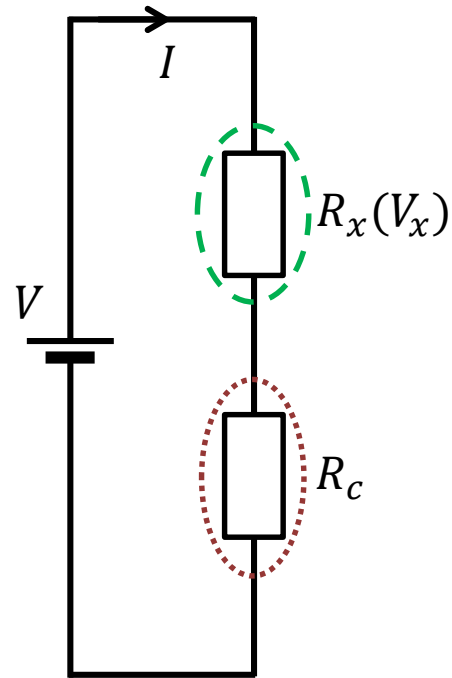
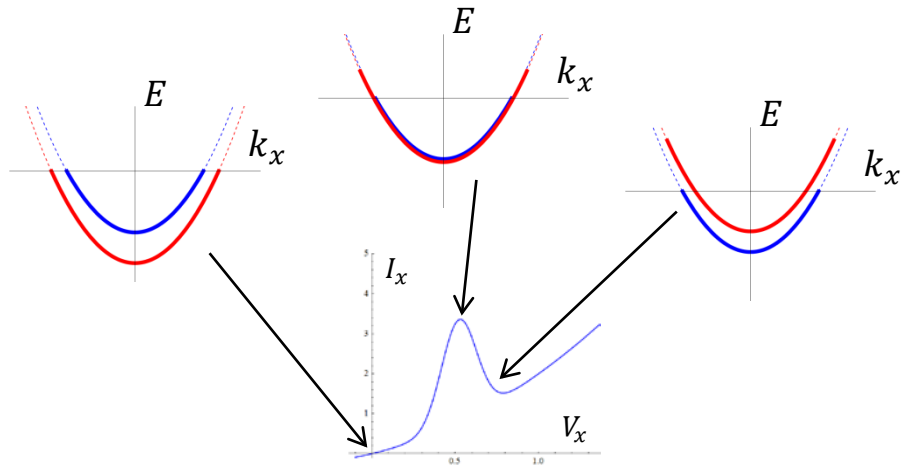
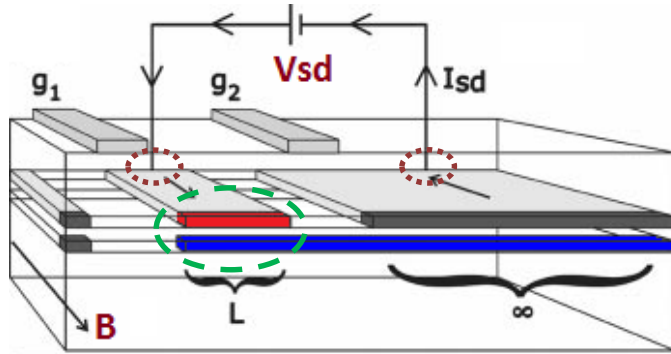


$$I = I_x$$

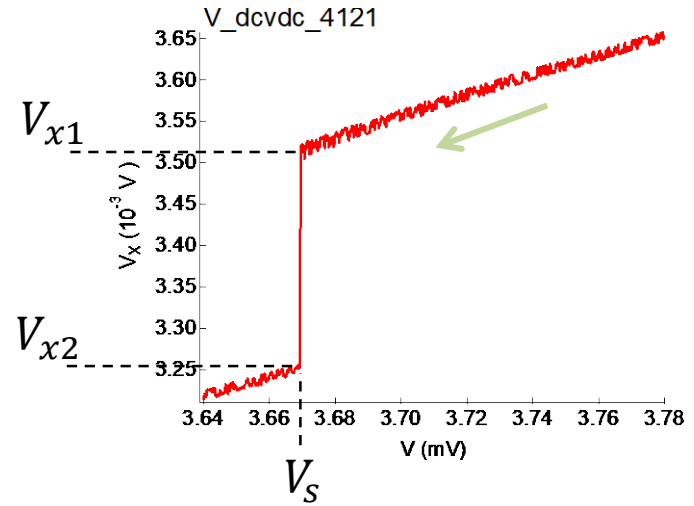
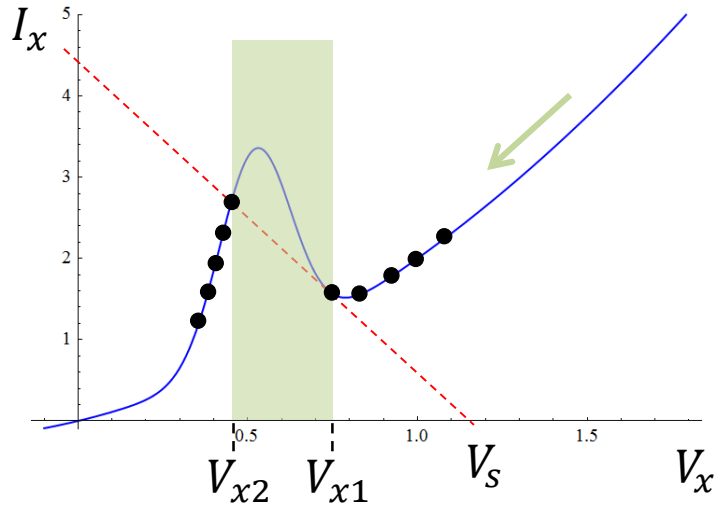
$$V = V_x + I R_c$$

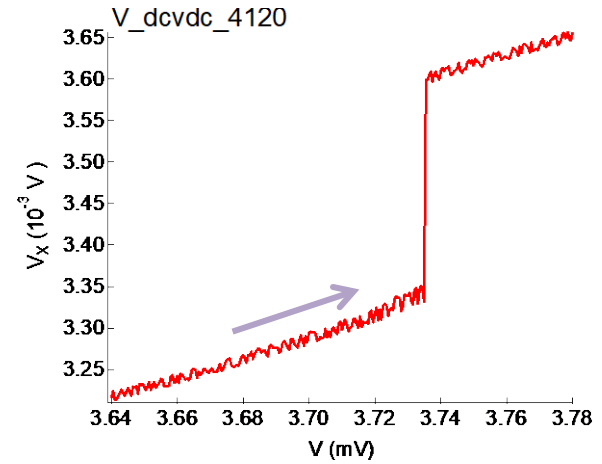
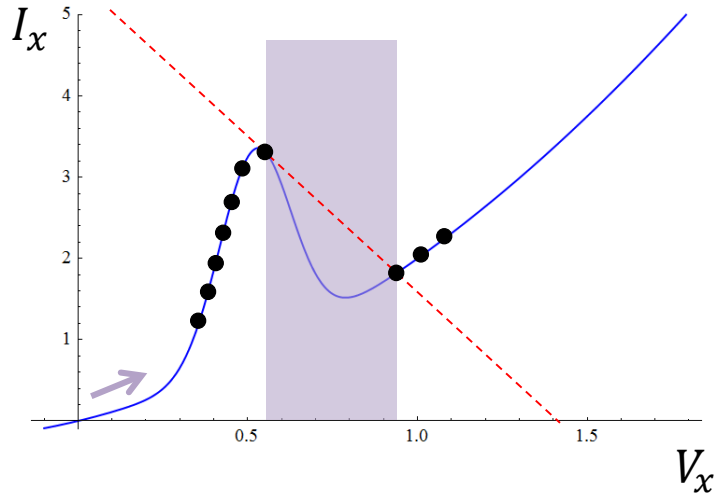
$$I = (V - V_x)/R_c$$

# CEO wires

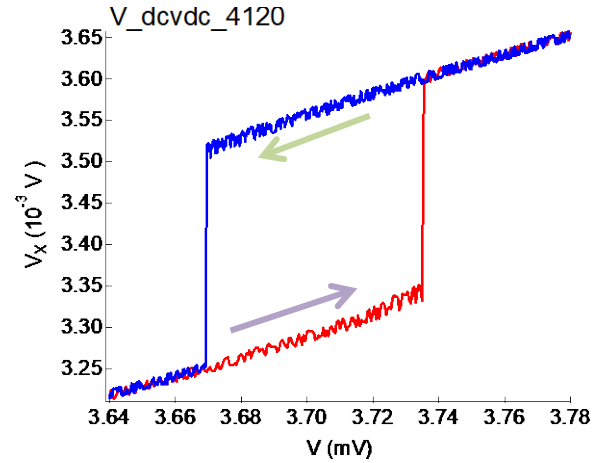
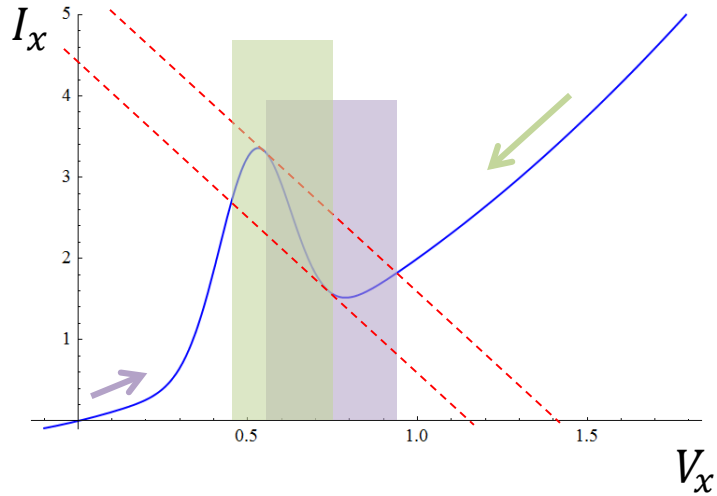






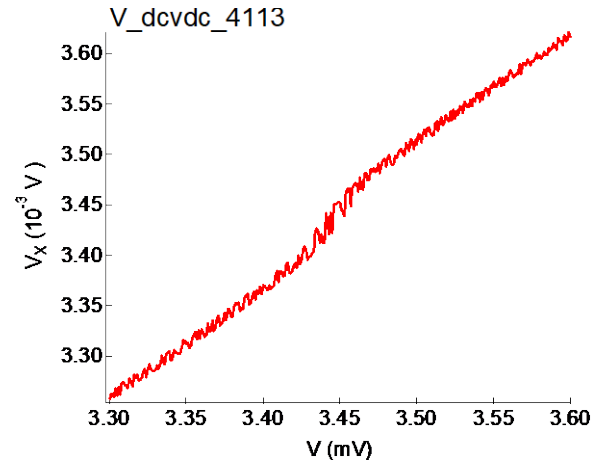
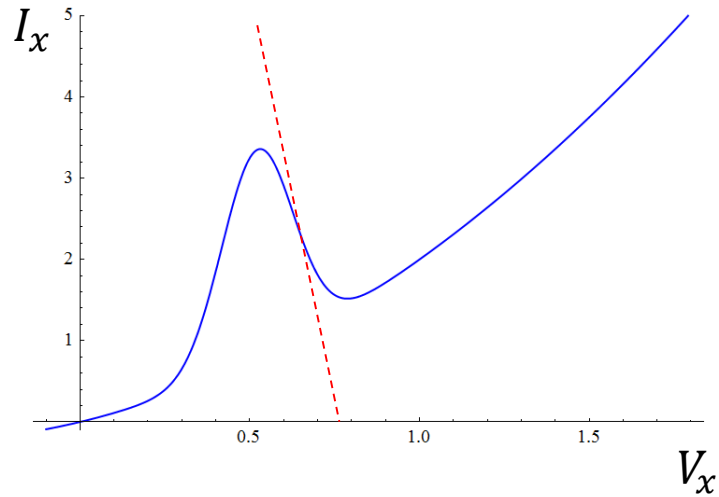


# Hysteresis

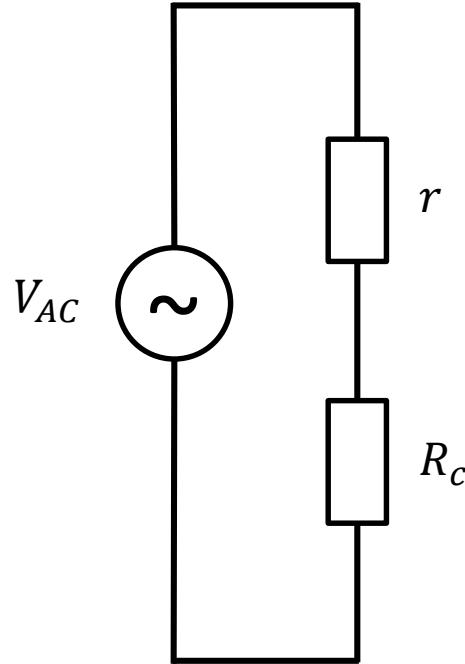
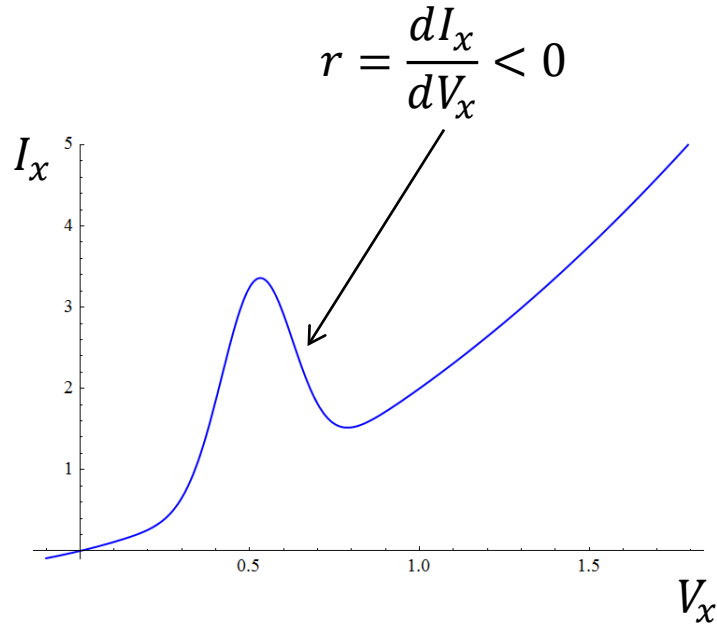




$$R_{c2} < R_{c1}$$



# NDC amplifier

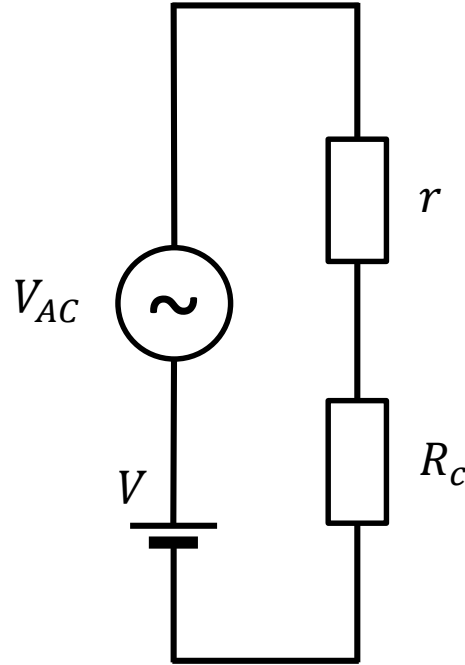
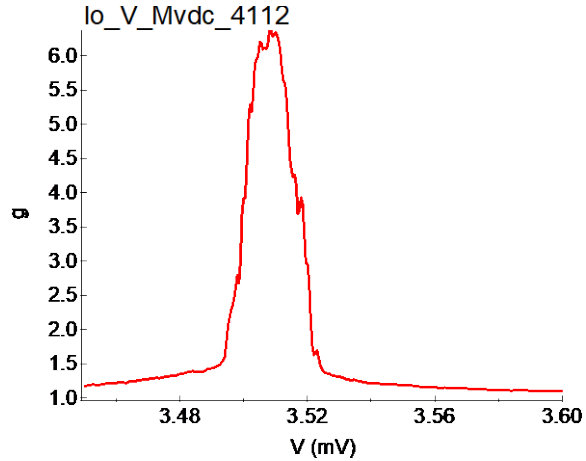


$$V_{x AC} = V_{AC} \frac{r}{R_c + r}$$

$$V_{x AC} = V_{AC} \frac{|r|}{R_c - |r|}$$

$$V_{x AC} = g V_{AC}$$

$$g = \frac{V_{x AC}}{V_{AC}}$$



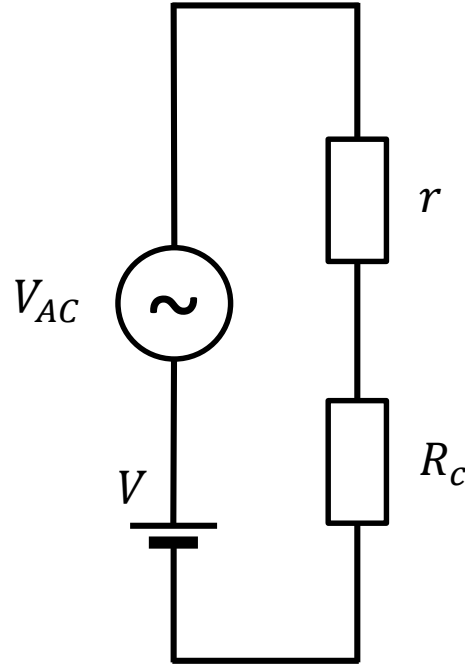
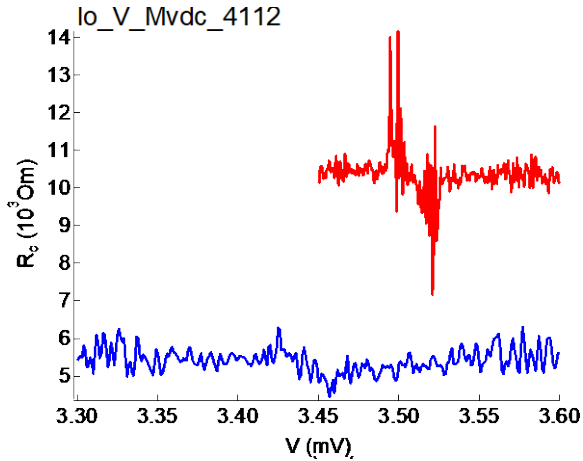
$$V_{x AC} = V_{AC} \frac{r}{R_C + r}$$

$$V_{x AC} = V_{AC} \frac{|r|}{R_C - |r|}$$

$$V_{x AC} = g V_{AC}$$

$$g = \frac{V_{x AC}}{V_{AC}}$$

# NDC amplifier



$$V_{x AC} = V_{AC} \frac{r}{R_C + r}$$

$$V_{x AC} = V_{AC} \frac{-|r|}{R_C - |r|}$$

$$V_{x AC} = g V_{AC}$$

$$g = \frac{V_{x AC}}{V_{AC}} = \frac{-|r|}{R_C - |r|}$$



## Conclusion

- Resonant tunneling in graphene
- Hysteresis, amplifications and oscillations based on NDC



